

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
40V	8.9mΩ @ V <sub>GS</sub> = 10V	49.0A
	13.5mΩ @ V <sub>GS</sub> = 4.5V	40.0A

## Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- Low R<sub>DS(ON)</sub> – Ensures On-State Losses are Minimized
- Excellent Q<sub>gd</sub> x R<sub>DS(ON)</sub> Product (FOM)
- Wettable Flank for Improved Optical Inspection
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **The DMTH47M2LFVWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

## Description and Applications

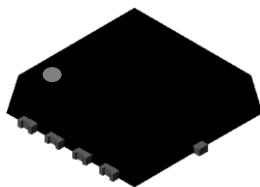
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power-management functions
- DC-DC converters

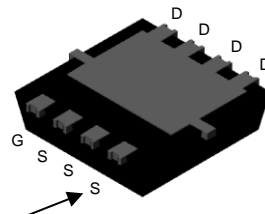
## Mechanical Data

- Package: PowerDI<sup>®</sup>3333-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.027 grams (Approximate)

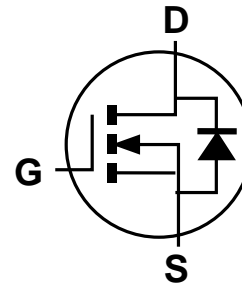
PowerDI3333-8 (SWP) (Type UX)



Top View



Pin 1 Bottom View



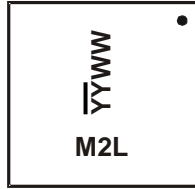
## Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMTH47M2LFVWQ-7	PowerDI3333-8 (SWP) (Type UX)	2,000	Tape & Reel
DMTH47M2LFVWQ-13	PowerDI3333-8 (SWP) (Type UX)	3,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information

PowerDI3333-8 (SWP) (Type UX)



M2L = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 23 = 2023)  
 WW = Week Code (01 to 53)

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	40	V	
Gate-Source Voltage		V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Note 5), V <sub>GS</sub> = 10V		I <sub>D</sub>	T <sub>C</sub> = +25°C T <sub>C</sub> = +100°C	49.0 34.7	A
Continuous Drain Current (Note 6), V <sub>GS</sub> = 10V	Steady State		T <sub>A</sub> = +25°C T <sub>A</sub> = +100°C	13.6 9.6	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	196	A	
Maximum Continuous Body Diode Forward Current (Note 5)		I <sub>S</sub>	49	A	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I <sub>SM</sub>	196	A	
Avalanche Current, L = 0.1mH		I <sub>AS</sub>	24	A	
Avalanche Energy, L = 0.1mH		E <sub>AS</sub>	28.8	mJ	

## Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	52	°C/W
Total Power Dissipation (Note 5)	T <sub>C</sub> = +25°C	P <sub>D</sub>	37.5	W
Thermal Resistance, Junction to Case (Note 5)		R <sub>θJC</sub>	4	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

Notes: 5. Thermal resistance from junction to soldering point (on the exposed drain pad).  
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 32V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.2	—	2.3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	6.6	8.9	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A
		—	8.9	13.5		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 10A
Diode Forward Voltage	V <sub>SD</sub>	—	0.87	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	881	—	pF	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	496	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	19.5	—		
Gate Resistance	R <sub>g</sub>	—	2.06	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	12.3	—	nC	V <sub>DS</sub> = 20V, I <sub>D</sub> = 20A
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	5.8	—		
Gate-Source Charge	Q <sub>gs</sub>	—	2.6	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	1.6	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.82	—	ns	V <sub>DD</sub> = 20V, V <sub>GS</sub> = 10V R <sub>g</sub> = 3Ω, I <sub>D</sub> = 20A
Turn-On Rise Time	t <sub>r</sub>	—	4.76	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	12.6	—		
Turn-Off Fall Time	t <sub>f</sub>	—	4.83	—		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	31.9	—	ns	I <sub>F</sub> = 20A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	25.0	—	nC	

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to production testing.

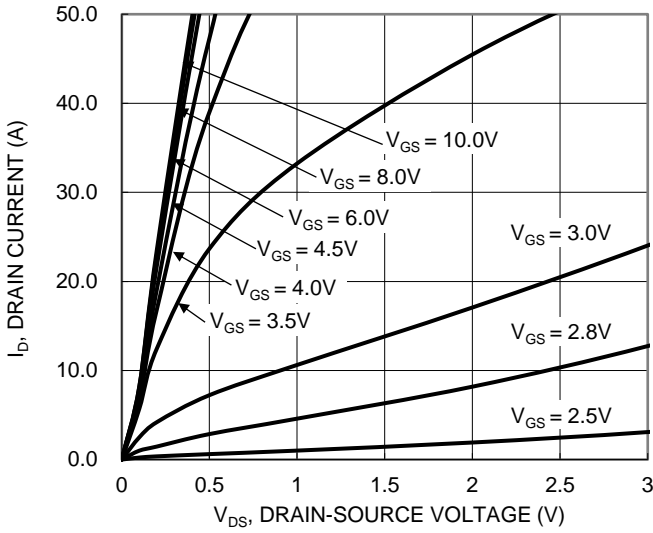


Figure 1. Typical Output Characteristic

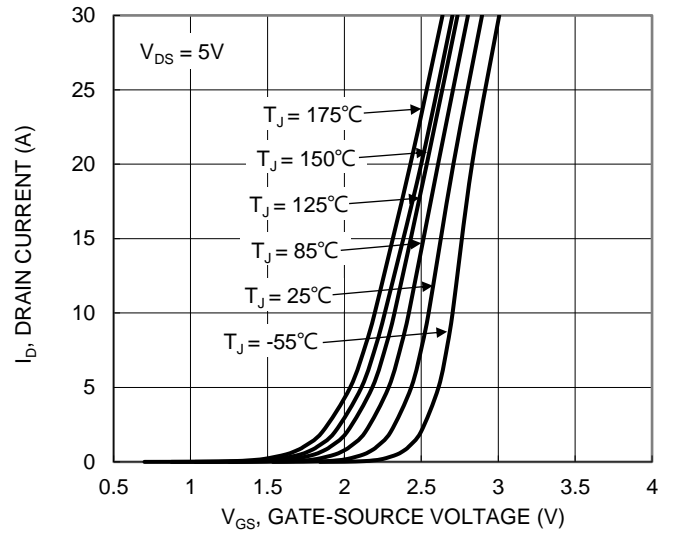


Figure 2. Typical Transfer Characteristic

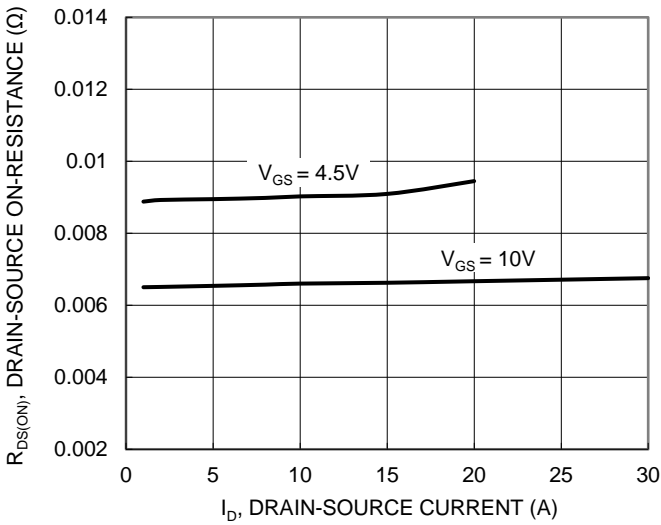


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

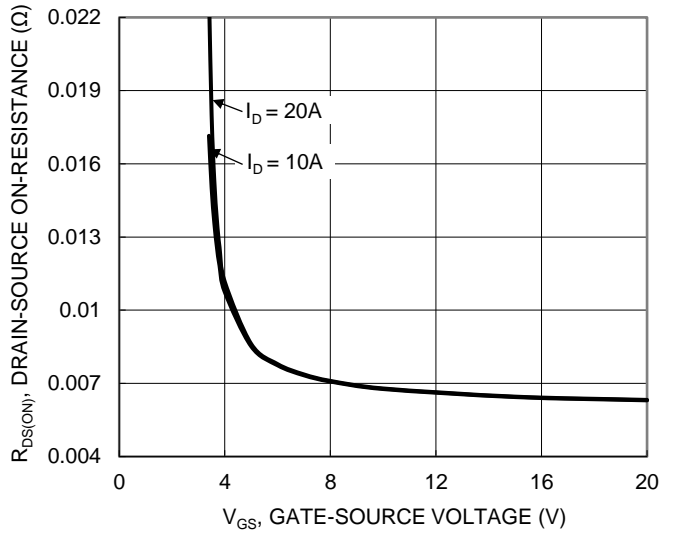


Figure 4. Typical Transfer Characteristic

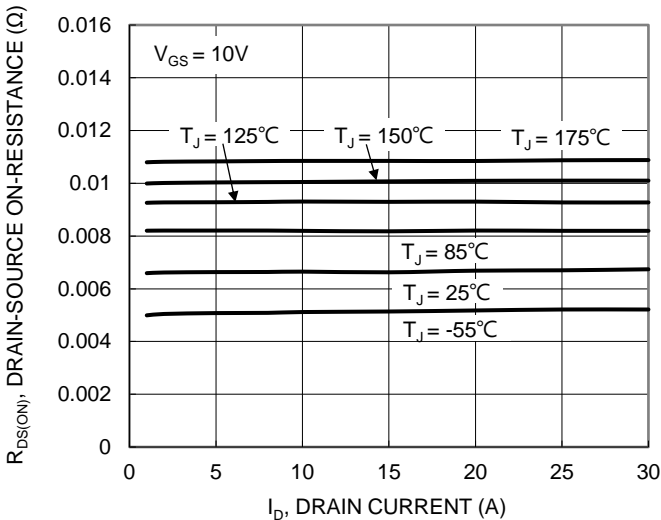


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

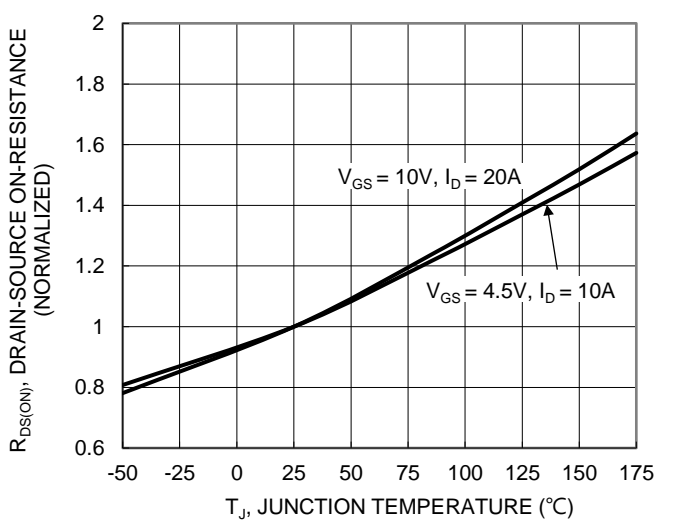


Figure 6. On-Resistance Variation with Junction Temperature

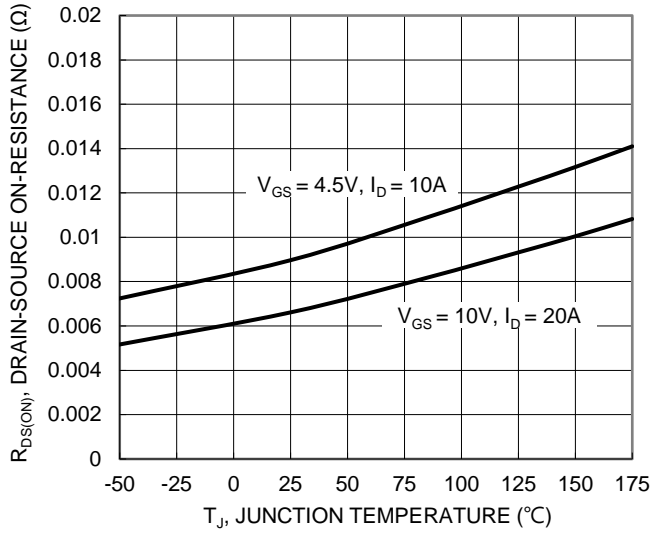


Figure 7. On-Resistance Variation with Junction Temperature

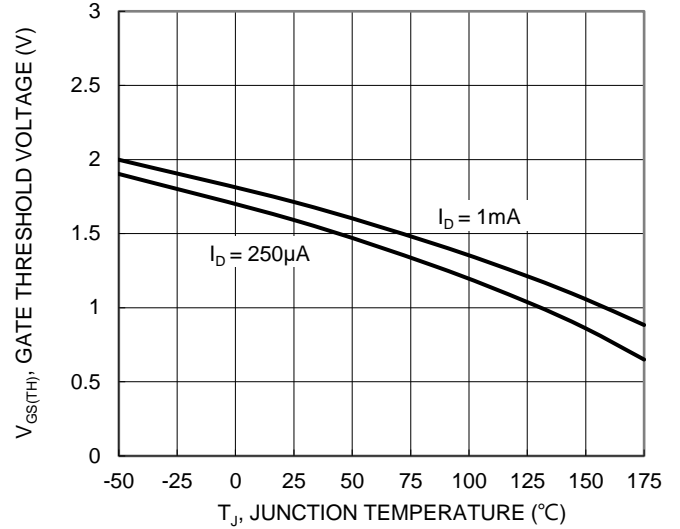


Figure 8. Gate Threshold Variation vs. Junction Temperature

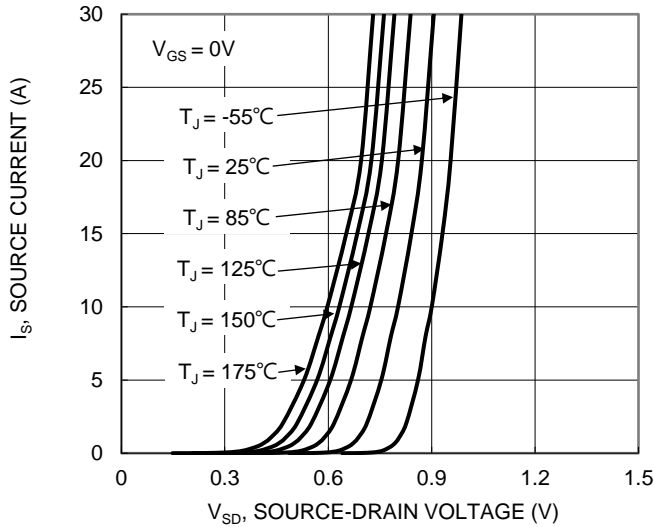


Figure 9. Diode Forward Voltage vs. Current

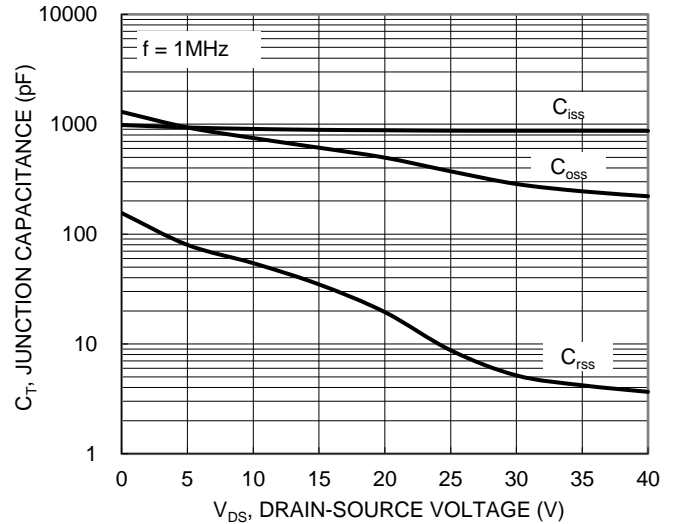


Figure 10. Typical Junction Capacitance

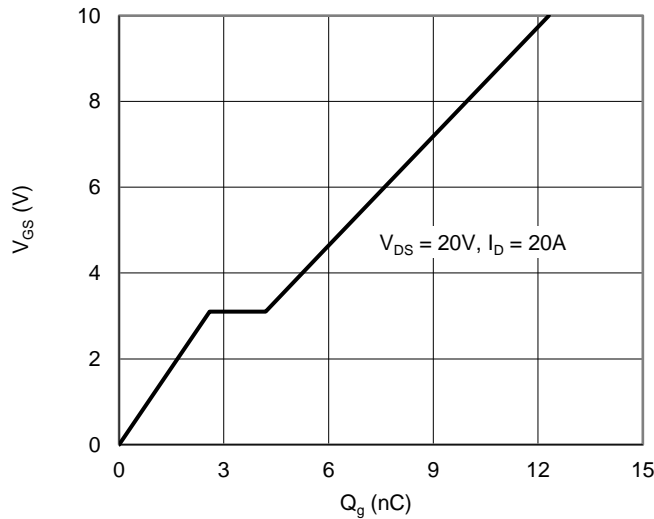


Figure 11. Gate Charge

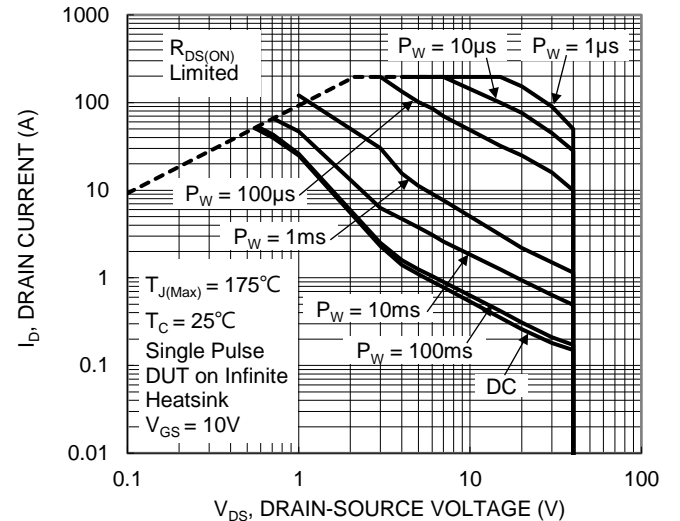


Figure 12. SOA, Safe Operation Area

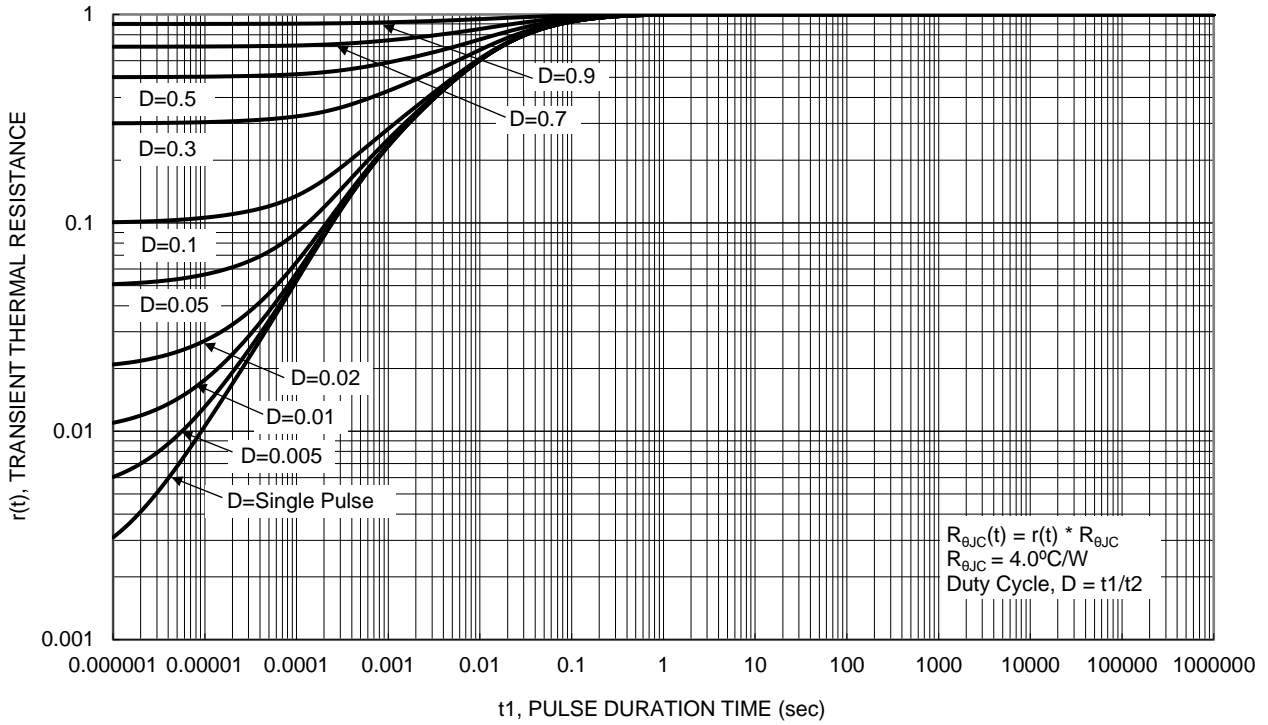
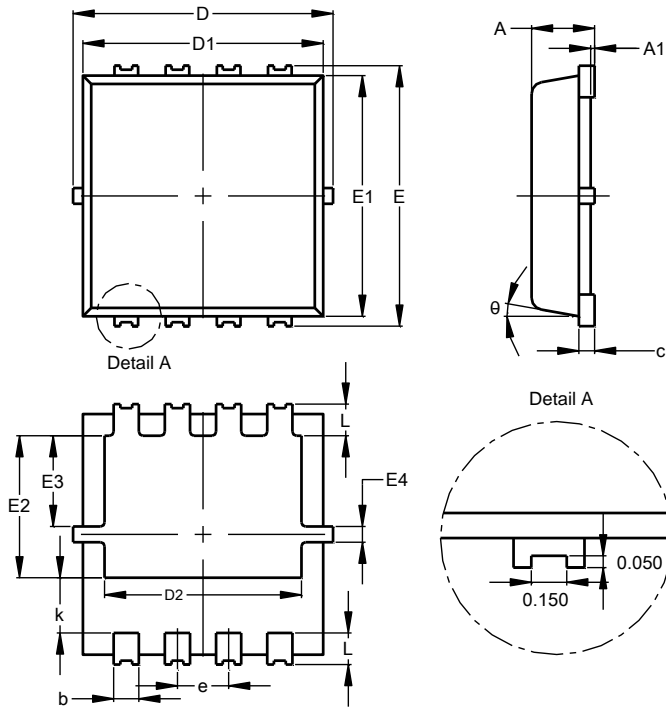


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8 (SWP) (Type UX)**

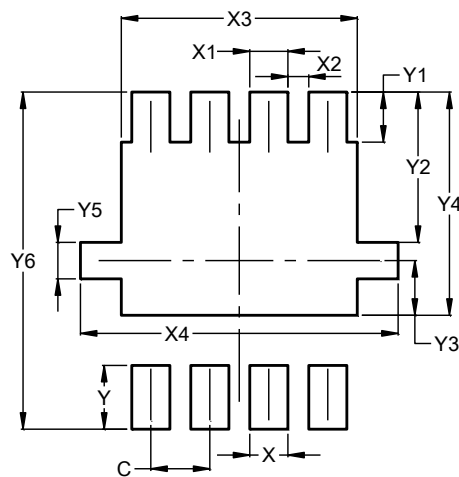


PowerDI3333-8 (SWP) (Type UX)			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	2.30	2.70	2.50
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E3	0.95	1.35	1.15
E4	0.10	0.30	0.20
e	--	--	0.65
k	0.50	0.90	0.70
L	0.30	0.50	0.40
θ	0°	12°	10°
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8 (SWP) (Type UX)**



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

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